

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device and a process for producing a semiconductor device using a gate electrode such as an SRAM, wherein a gate electrode pattern is formed with fidelity to a reticle pattern through no complicated layout design and the gate electrode pattern is formed in an area smaller than that of a conventional semiconductor device. In a lithographic step using a reticle pattern provided with substantially linear gate electrode patterns, a projecting portion in which at least a part of a contact region is arranged is formed such that it is included in almost the center of a long side of a linear gate electrode pattern and a concave portion facing at least the entire length of the projecting portion is formed such that it is included in a long side opposite to the projecting portion between transistor regions of a reticle pattern. In miniaturization technologies, the fidelity of a pattern in a process for the production of a semiconductor device can be improved by the reticle pattern having the concave portion.